

Fernando A. Ponce

List of Publications by Year in descending order

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354
papers

13,122
citations

28242

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104
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357
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357
docs citations

357
times ranked

7559
citing authors

#	ARTICLE	IF	CITATIONS
1	Nitride-based semiconductors for blue and green light-emitting devices. <i>Nature</i> , 1997, 386, 351-359.	13.7	1,550
2	High dislocation densities in high efficiency GaN-based light-emitting diodes. <i>Applied Physics Letters</i> , 1995, 66, 1249-1251.	1.5	961
3	Defects in single-crystal silicon induced by hydrogenation. <i>Physical Review B</i> , 1987, 35, 4166-4169.	1.1	432
4	Spatial distribution of the luminescence in GaN thin films. <i>Applied Physics Letters</i> , 1996, 68, 57-59.	1.5	361
5	Luminescence from stacking faults in gallium nitride. <i>Applied Physics Letters</i> , 2005, 86, 021908.	1.5	315
6	Self-limiting oxidation for fabricating sub-5 nm silicon nanowires. <i>Applied Physics Letters</i> , 1994, 64, 1383-1385.	1.5	270
7	Epitaxial MgO on Si(001) for BaCu thin film growth by pulsed laser deposition. <i>Applied Physics Letters</i> , 1991, 58, 2294-2296.	1.5	237
8	Determination of lattice polarity for growth of GaN bulk single crystals and epitaxial layers. <i>Applied Physics Letters</i> , 1996, 69, 337-339.	1.5	227
9	Edge and screw dislocations as nonradiative centers in InGaN/GaN quantum well luminescence. <i>Applied Physics Letters</i> , 2001, 78, 2691-2693.	1.5	218
10	Microstructure of GaN epitaxy on SiC using AlN buffer layers. <i>Applied Physics Letters</i> , 1995, 67, 410-412.	1.5	200
11	Slip systems and misfit dislocations in InGaN epilayers. <i>Applied Physics Letters</i> , 2003, 83, 5187-5189.	1.5	194
12	Characterization of dislocations in GaN by transmission electron diffraction and microscopy techniques. <i>Applied Physics Letters</i> , 1996, 69, 770-772.	1.5	184
13	Improvement of peak quantum efficiency and efficiency droop in III-nitride visible light-emitting diodes with an InAlN electron-blocking layer. <i>Applied Physics Letters</i> , 2010, 96, .	1.5	183
14	Self-limiting oxidation of Si nanowires. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1993, 11, 2532.	1.6	149
15	Initial stages of epitaxial growth of GaAs on (100) silicon. <i>Journal of Applied Physics</i> , 1987, 61, 1856-1859.	1.1	148
16	Crystalline structure of AlGaIn epitaxy on sapphire using AlN buffer layers. <i>Applied Physics Letters</i> , 1994, 65, 2302-2304.	1.5	140
17	Microstructure and electronic properties of InGaIn alloys. <i>Physica Status Solidi (B): Basic Research</i> , 2003, 240, 273-284.	0.7	131
18	MOVPE growth of GaN on Si(111) substrates. <i>Journal of Crystal Growth</i> , 2003, 248, 556-562.	0.7	125

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19	Exciton freeze-out and thermally activated relaxation at local potential fluctuations in thick Al _x Ga _{1-x} N layers. Journal of Applied Physics, 2004, 95, 4670-4674.	1.1	119
20	Metalorganic chemical vapor phase epitaxy of gallium-nitride on silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1583-1606.	0.8	116
21	Strained Ga _x In _{1-x} P/(AlGa) _{0.5} In _{0.5} P heterostructures and quantum-well laser diodes. IEEE Journal of Quantum Electronics, 1994, 30, 593-607.	1.0	115
22	Atomic arrangement at the AlN/Si (111) interface. Applied Physics Letters, 2003, 83, 860-862.	1.5	114
23	Dislocation annihilation by silicon delta-doping in GaN epitaxy on Si. Applied Physics Letters, 2002, 81, 4712-4714.	1.5	109
24	Homoepitaxy of GaN on polished bulk single crystals by metalorganic chemical vapor deposition. Applied Physics Letters, 1996, 68, 917-919.	1.5	107
25	Hydrogen in crystalline semiconductors. Physica B: Condensed Matter, 1991, 170, 3-20.	1.3	104
26	Thermodynamic and kinetic considerations on the equilibrium shape for thermally induced microdefects in Czochralski silicon. Journal of Applied Physics, 1986, 59, 3255-3266.	1.1	96
27	Defects and Interfaces in GaN Epitaxy. MRS Bulletin, 1997, 22, 51-57.	1.7	93
28	Oxidation of sub-50 nm Si columns for light emission study. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1992, 10, 2846.	1.6	92
29	Improvement of quantum efficiency by employing active-layer-friendly lattice-matched InAlN electron blocking layer in green light-emitting diodes. Applied Physics Letters, 2010, 96, .	1.5	89
30	Observation of coreless dislocations in In _± -GaN. Journal of Crystal Growth, 1997, 178, 201-206.	0.7	87
31	Reactions at the interfaces of thin films of Y ₂ O ₃ and ZrO ₂ oxides with Si substrates. Journal of Applied Physics, 1991, 69, 2176-2182.	1.1	85
32	Ion milled tips for scanning tunneling microscopy. Applied Physics Letters, 1987, 50, 696-698.	1.5	83
33	Efficiency droop due to electron spill-over and limited hole injection in III-nitride visible light-emitting diodes employing lattice-matched InAlN electron blocking layers. Applied Physics Letters, 2012, 101, .	1.5	80
34	Pulsed lateral epitaxial overgrowth of aluminum nitride on sapphire substrates. Applied Physics Letters, 2006, 89, 081905.	1.5	79
35	Low-threshold stimulated emission at 249 nm and 256 nm from AlGaIn-based multiple-quantum-well lasers grown on sapphire substrates. Applied Physics Letters, 2014, 105, .	1.5	78
36	Deep-ultraviolet lasing at 243 nm from photo-pumped AlGaIn/AlN heterostructure on AlN substrate. Applied Physics Letters, 2013, 102, .	1.5	77

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37	Preparation of oriented Biâ€Caâ€Srâ€Cuâ€O thin films using pulsed laser deposition. Applied Physics Letters, 1988, 53, 337-339.	1.5	76
38	Atomic arrangement at the AlN/SiC interface. Physical Review B, 1996, 53, 7473-7478.	1.1	75
39	Direct imaging of impurityâ€induced Raman scattering in GaN. Applied Physics Letters, 1996, 69, 2650-2652.	1.5	71
40	Light emission and microstructure of Mg-doped AlGaIn grown on patterned sapphire. Applied Physics Letters, 2003, 82, 349-351.	1.5	71
41	Prismatic stacking faults in epitaxially laterally overgrown GaN. Applied Physics Letters, 2006, 88, 141912.	1.5	69
42	Synthesis and luminescence properties of ZnO nanostructures produced by the solâ€gel method. Journal of Crystal Growth, 2008, 310, 599-603.	0.7	64
43	Misfit Strain Relaxation by Stacking Fault Generation in InGaIn Quantum Wells Grown on <i>m</i> -Plane GaN. Applied Physics Express, 0, 2, 041002.	1.1	64
44	Structure of thermally induced microdefects in Czochralski silicon after highâ€temperature annealing. Applied Physics Letters, 1983, 43, 1051-1053.	1.5	63
45	Atomic motion on the surface of a cadmium telluride single crystal. Nature, 1981, 290, 386-388.	13.7	62
46	Interface structure in heteroepitaxial CdTe on GaAs(100). Surface Science, 1986, 168, 564-570.	0.8	62
47	Resonant tunneling in GaAs/AlAs heterostructures grown by metalorganic chemical vapor deposition. Applied Physics Letters, 1985, 46, 285-287.	1.5	61
48	Generation of misfit dislocations by basal-plane slip in InGaInâ€GaIn heterostructures. Applied Physics Letters, 2006, 89, 201911.	1.5	61
49	Structural and optical properties of nonpolar GaIn thin films. Applied Physics Letters, 2008, 92, .	1.5	61
50	Control of quantum-confined Stark effect in InGaInâ€GaIn multiple quantum well active region by p-type layer for III-nitride-based visible light emitting diodes. Applied Physics Letters, 2008, 92, .	1.5	60
51	Engineered Schottky barrier diodes for the modification and control of Schottky barrier heights. Journal of Applied Physics, 1987, 61, 5159-5169.	1.1	59
52	Effect of interface chemistry on the growth of ZnSe on the Si(100) surface. Physical Review B, 1992, 45, 13400-13406.	1.1	58
53	Low Stokes shift in thick and homogeneous InGaIn epilayers. Applied Physics Letters, 2002, 80, 550-552.	1.5	58
54	High critical current densities in epitaxial YBaCuO thin films on siliconâ€sapphire. Applied Physics Letters, 1991, 58, 2432-2434.	1.5	57

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55	Epitaxial BaTiO ₃ /MgO Structure Grown on GaAs(100) by Pulsed Laser Deposition*. Japanese Journal of Applied Physics, 1993, 32, 4099-4102.	0.8	57
56	Mapping electrostatic potential across an AlGaIn/InGaIn/AlGaIn diode by electron holography. Applied Physics Letters, 2000, 76, 3055-3057.	1.5	57
57	Dynamic observation of defect annealing in CdTe at lattice resolution. Nature, 1982, 298, 127-131.	13.7	55
58	Excimer-laser-induced crystallization of hydrogenated amorphous silicon. Applied Physics Letters, 1990, 57, 2222-2224.	1.5	54
59	Fault-free silicon at the silicon/sapphire interface. Applied Physics Letters, 1982, 41, 371-373.	1.5	53
60	Demonstration of transverse-magnetic deep-ultraviolet stimulated emission from AlGaIn multiple-quantum-well lasers grown on a sapphire substrate. Applied Physics Letters, 2015, 106, .	1.5	53
61	Carrier localization and nonradiative recombination in yellow emitting InGaIn quantum wells. Applied Physics Letters, 2010, 96, .	1.5	52
62	Investigation of GaIn-on-GaIn vertical p-n diode with regrown p-GaIn by metalorganic chemical vapor deposition. Applied Physics Letters, 2018, 113, .	1.5	52
63	Fine structure of AlN/AlGaIn superlattice grown by pulsed atomic-layer epitaxy for dislocation filtering. Applied Physics Letters, 2005, 87, 211915.	1.5	49
64	Comprehensive study of the electronic and optical behavior of highly degenerate p-type Mg-doped GaIn and AlGaIn. Journal of Applied Physics, 2015, 117, .	1.1	49
65	High Voltage Vertical GaIn p-n Diodes With Hydrogen-Plasma Based Guard Rings. IEEE Electron Device Letters, 2020, 41, 127-130.	2.2	49
66	Measurement of the piezoelectric field across strained InGaIn/GaIn layers by electron holography. Solid State Communications, 1999, 111, 281-285.	0.9	48
67	Determination of the atomic structure of inversion domain boundaries in $\hat{\Gamma}_2$ -GaIn by transmission electron microscopy. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1998, 77, 273-286.	0.7	47
68	Study of charge distribution across interfaces in GaIn/InGaIn/GaIn single quantum wells using electron holography. Journal of Applied Physics, 2002, 91, 9856.	1.1	47
69	Growth of high-quality AlN layers on sapphire substrates at relatively low temperatures by metalorganic chemical vapor deposition. Physica Status Solidi (B): Basic Research, 2015, 252, 1089-1095.	0.7	46
70	Lattice structure at ZnSe/GaAs heterojunction interfaces prepared by organometallic chemical vapor deposition. Thin Solid Films, 1983, 104, 133-143.	0.8	45
71	Origins of unintentional incorporation of gallium in AlInN layers during epitaxial growth, part I: Growth of AlInN on AlN and effects of prior coating. Journal of Crystal Growth, 2014, 388, 137-142.	0.7	45
72	Polychromatic light emission from single InGaIn quantum wells grown on pyramidal GaIn facets. Applied Physics Letters, 2005, 87, 131911.	1.5	44

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73	Origins of unintentional incorporation of gallium in InAlN layers during epitaxial growth, part II: Effects of underlying layers and growth chamber conditions. <i>Journal of Crystal Growth</i> , 2014, 388, 143-149.	0.7	44
74	Determination by Electron Holography of the Electronic Charge Distribution at Threading Dislocations in Epitaxial GaN. <i>Physica Status Solidi A</i> , 2002, 192, 407-411.	1.7	42
75	Localized states at InGaN/GaN quantum well interfaces. <i>Applied Physics Letters</i> , 1999, 75, 3835-3837.	1.5	41
76	Bright, Crack-Free InGaN/GaN Light Emitters on Si(111). <i>Physica Status Solidi A</i> , 2002, 192, 308-313.	1.7	41
77	Electron Holography Studies of the Charge on Dislocations in GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 234, 924-930.	0.7	40
78	Misfit dislocations in GaAs heteroepitaxy on (001) Si. <i>Journal of Crystal Growth</i> , 1990, 106, 157-165.	0.7	38
79	Misfit Dislocation Generation in InGaN Epilayers on Free-Standing GaN. <i>Japanese Journal of Applied Physics</i> , 2006, 45, L549-L551.	0.8	38
80	Temperature dependence of the crystalline quality of AlN layer grown on sapphire substrates by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2015, 414, 76-80.	0.7	38
81	Structural and optical characterization of nonpolar GaN/AlN quantum wells. <i>Applied Physics Letters</i> , 2003, 83, 653-655.	1.5	37
82	Localization versus field effects in single InGaN quantum wells. <i>Applied Physics Letters</i> , 2004, 84, 58-60.	1.5	36
83	Sub-250-nm low-threshold deep-ultraviolet AlGaIn-based heterostructure laser employing HfO ₂ /SiO ₂ dielectric mirrors. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	36
84	Low-temperature growth of InGaIn films over the entire composition range by MBE. <i>Journal of Crystal Growth</i> , 2015, 425, 115-118.	0.7	36
85	Imaging of the silicon on sapphire interface by high-resolution transmission electron microscopy. <i>Applied Physics Letters</i> , 1981, 38, 439-441.	1.5	35
86	Characterisation of dislocations, nanopipes and inversion domains in GaN by transmission electron microscopy. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1997, 50, 76-81.	1.7	35
87	Highly luminescent, high-indium-content InGaIn film with uniform composition and full misfit-strain relaxation. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	35
88	100-nm thick single-phase wurtzite BAlN films with boron contents over 10%. <i>Physica Status Solidi (B): Basic Research</i> , 2017, 254, 1600699.	0.7	35
89	Summary Abstract: High resolution electron microscopy of CaF ₂ /silicon interfaces. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1986, 4, 1121.	1.6	34
90	Simple ion milling preparation of ¹¹¹ tungsten tips. <i>Applied Physics Letters</i> , 1989, 54, 1223-1225.	1.5	34

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91	Native tellurium dioxide layer on cadmium telluride: A high-resolution electron microscopy study. Applied Physics Letters, 1981, 39, 951-953.	1.5	33
92	Growth of self-assembled GaN quantum dots via the vapor-liquid-solid mechanism. Applied Physics Letters, 2002, 81, 3236-3238.	1.5	33
93	Crystal orientation dependence of the electrical transport and lattice structure of zinc selenide films grown by metalorganic chemical vapor deposition. Journal of Applied Physics, 1985, 58, 1548-1553.	1.1	31
94	Effects of heavy boron doping upon oxygen precipitation in Czochralski silicon. Journal of Applied Physics, 1988, 64, 4454-4465.	1.1	31
95	Characterization of OMVPE-Grown AlGaInN Heterostructures. Materials Research Society Symposia Proceedings, 1996, 449, 509.	0.1	31
96	Effect of layer thickness on the electrostatic potential in InGaN quantum wells. Applied Physics Letters, 2004, 85, 4651-4653.	1.5	31
97	Growth of GaN on ZrB ₂ substrate by metal-organic vapor phase epitaxy. Applied Surface Science, 2003, 216, 502-507.	3.1	30
98	Atomic arrangement at the Au-p-GaN interface in low-resistance contacts. Applied Physics Letters, 2004, 85, 6143-6145.	1.5	30
99	Compositional instability in InAlN/GaN lattice-matched epitaxy. Applied Physics Letters, 2012, 100, .	1.5	30
100	Microstructural properties of Eu-doped GaN luminescent powders. Applied Physics Letters, 2002, 81, 1993-1995.	1.5	29
101	Sub 250-nm deep-UV AlGaInN distributed Bragg reflectors. Applied Physics Letters, 2017, 110, .	1.5	29
102	The effect of a Ga prelayer on the beginning of GaAs epitaxy on Si. Journal of Applied Physics, 1988, 64, 3472-3475.	1.1	28
103	Polarity determination and atomic arrangements at a GaN/SiC interface using high-resolution image matching. Applied Physics Letters, 2000, 76, 822-824.	1.5	28
104	Simulations, Practical Limitations, and Novel Growth Technology for InGaN-Based Solar Cells. IEEE Journal of Photovoltaics, 2014, 4, 601-606.	1.5	28
105	Plasticity and optical properties of GaN under highly localized nanoindentation stress fields. Journal of Applied Physics, 2017, 121, .	1.1	28
106	Implantation-and etching-free high voltage vertical GaN p-n diodes terminated by plasma-hydrogenated p-GaN: revealing the role of thermal annealing. Applied Physics Express, 2019, 12, 051015.	1.1	28
107	Graded-thickness samples for molecular beam epitaxial growth studies of GaAs/Si heteroepitaxy. Applied Physics Letters, 1988, 52, 1779-1781.	1.5	27
108	Atomic arrangement at the AlN/ZrB ₂ interface. Applied Physics Letters, 2002, 81, 3182-3184.	1.5	27

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109	Dislocation generation at the coalescence of aluminum nitride lateral epitaxy on shallow-grooved sapphire substrates. Applied Physics Letters, 2007, 90, 221909.	1.5	27
110	High-resolution transmission electron microscopy of 60[ddot] dislocations in si-GaAs. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1989, 59, 1045-1058.	0.7	26
111	Mapping the electrostatic potential across AlGaN~·AlN~·GaN heterostructures using electron holography. Applied Physics Letters, 2007, 90, 032101.	1.5	26
112	Blue light emitting diodes grown on freestanding (11-20) a-plane GaN substrates. Applied Physics Letters, 2008, 92, 011123.	1.5	26
113	Refractory In\$_{x}\$ Ga\$_{1-x}\$ N Solar Cells for High-Temperature Applications. IEEE Journal of Photovoltaics, 2017, 7, 1646-1652.	1.5	26
114	CdCl ₂ passivation of polycrystalline CdMgTe and CdZnTe absorbers for tandem photovoltaic cells. Journal of Applied Physics, 2018, 123, .	1.1	26
115	Defect formation near GaN surfaces and interfaces. Physica B: Condensed Matter, 1999, 273-274, 70-74.	1.3	25
116	Optoelectronic and microstructure attributes of epitaxial SrTiO ₃ on Si. Journal of Applied Physics, 2005, 97, 014101.	1.1	25
117	Effect of internal electrostatic fields in InGaN quantum wells on the properties of green light emitting diodes. Applied Physics Letters, 2007, 91, .	1.5	25
118	Non-uniform Mg distribution in GaN epilayers grown on mesa structures for applications in GaN power electronics. Applied Physics Letters, 2019, 114, .	1.5	25
119	GaN Vertical-Channel Junction Field-Effect Transistors With Regrown p-GaN by MOCVD. IEEE Transactions on Electron Devices, 2020, 67, 3972-3977.	1.6	25
120	Use of ZnSe as an interlayer for GaAs growth on Si. Applied Physics Letters, 1992, 61, 195-197.	1.5	24
121	Observation of coreless edge and mixed dislocations in Mg-doped Al _{0.03} Ga _{0.97} N. Applied Physics Letters, 2002, 81, 4541-4543.	1.5	24
122	Role of the buffer layer thickness on the formation of basal plane stacking faults in a-plane GaN epitaxy on r-sapphire. Applied Physics Letters, 2008, 93, 011901.	1.5	24
123	Optimization of growth conditions for InGaAs/InAlAs/InP quantum cascade lasers by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2011, 316, 75-80.	0.7	24
124	Onset of surface stimulated emission at 260~nm from AlGaN multiple quantum wells. Applied Physics Letters, 2015, 107, .	1.5	24
125	Interface effects in amorphous silicon/nitride multilayers. Journal of Non-Crystalline Solids, 1985, 77-78, 995-998.	1.5	23
126	Depth-resolved electron-excited nanoscale-luminescence spectroscopy studies of defects near GaN/InGaN/GaN quantum wells. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 2545.	1.6	23

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127	A Comparison of Rutherford Backscattering Spectroscopy and X-Ray Diffraction to Determine the Composition of Thick InGaN Epilayers. <i>Physica Status Solidi (B): Basic Research</i> , 2001, 228, 41-44.	0.7	23
128	Metal-Organic Hydride Vapor Phase Epitaxy of Al _x Ga _{1-x} N Films over Sapphire. <i>Japanese Journal of Applied Physics</i> , 2007, 46, L752-L754.	0.8	23
129	High-resolution lattice imaging of cadmium telluride. <i>Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties</i> , 1982, 45, 693-711.	0.7	22
130	Nanopipes and Inversion Domains in High-Quality GaN Epitaxial Layers. <i>Materials Research Society Symposia Proceedings</i> , 1996, 449, 405.	0.1	22
131	Microstructure of InGaN Quantum Wells. <i>Materials Research Society Symposia Proceedings</i> , 1997, 482, 31.	0.1	22
132	High-Quality GaN heteroepitaxial films grown by metalorganic chemical vapor deposition. <i>Journal of Electronic Materials</i> , 1995, 24, 257-261.	1.0	21
133	Microscopic correlation of redshifted luminescence and surface defects in thick In _x Ga _{1-x} N layers. <i>Applied Physics Letters</i> , 2002, 80, 3524-3526.	1.5	21
134	Defect and stress control of AlGaIn for fabrication of high performance UV light emitters. <i>Physica Status Solidi A</i> , 2004, 201, 2679-2685.	1.7	21
135	Optical properties of highly luminescent zinc oxide tetrapod powders. <i>Applied Physics Letters</i> , 2007, 91, 121905.	1.5	21
136	Atomic Arrangement at the AlN/Si(110) Interface. <i>Applied Physics Express</i> , 0, 1, 061104.	1.1	21
137	Comparative Study on MOCVD Growth of a-Plane GaN Films on r-Plane Sapphire Substrates Using GaN, AlGaIn, and AlN Buffer Layers. <i>Journal of Electronic Materials</i> , 2009, 38, 1938-1943.	1.0	21
138	Optically pumped vertical-cavity surface-emitting laser at 374.9 nm with an electrically conducting n-type distributed Bragg reflector. <i>Applied Physics Express</i> , 2016, 9, 111002.	1.1	21
139	Selective area regrowth and doping for vertical gallium nitride power devices: Materials challenges and recent progress. <i>Materials Today</i> , 2021, 49, 296-323.	8.3	21
140	Critical thickness determination of InAs, InP and GaP on GaAs by X-ray interference effect and transmission electron microscopy. <i>Journal of Crystal Growth</i> , 1993, 131, 465-469.	0.7	20
141	Epitaxial growth of Al _x Ga _{1-x} N on Si(111) via a ZrB ₂ (0001) buffer layer. <i>Applied Physics Letters</i> , 2004, 84, 3510-3512.	1.5	20
142	Strain Relaxation Mechanisms in AlGaIn Epitaxy on AlN Templates. <i>Applied Physics Express</i> , 2010, 3, 111003.	1.1	20
143	Time-resolved cathodoluminescence of Mg-doped GaN. <i>Applied Physics Letters</i> , 2008, 93, .	1.5	19
144	In-plane polarization of GaN-based heterostructures with arbitrary crystal orientation. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010, 207, 2226-2232.	0.8	19

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145	The effect of InGaN underlayers on the electronic and optical properties of InGaN/GaN quantum wells. Applied Physics Letters, 2013, 102, .	1.5	19
146	A review of the synthesis of reduced defect density In _x Ga _{1-x} N for all indium compositions. Solid-State Electronics, 2017, 136, 3-11.	0.8	19
147	Dopant profiling in p-i-n GaN structures using secondary electrons. Journal of Applied Physics, 2019, 126, .	1.1	19
148	Microscopic aspects of oxygen precipitation in silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1989, 4, 11-17.	1.7	18
149	Gallium-nitride-based devices on silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1940-1949.	0.8	18
150	Mechanism of H ₂ pre-annealing on the growth of GaN on sapphire by MOVPE. Applied Surface Science, 2003, 216, 585-589.	3.1	17
151	Correlation of spectral luminescence with threading dislocations in green-light-emitting InGaN quantum wells. Applied Physics Letters, 2007, 90, 231901.	1.5	17
152	Highly conductive modulation doped composition graded p-AlGa _x (AlN)/Ga _{1-x} N multiheterostructures grown by metalorganic vapor phase epitaxy. Journal of Applied Physics, 2009, 106, .	1.1	17
153	Ammonothermal growth of high-quality GaN crystals on HVPE template seeds. Journal of Crystal Growth, 2011, 318, 1030-1033.	0.7	17
154	InAs quantum dot growth on Al _x Ga _{1-x} As by metalorganic vapor phase epitaxy for intermediate band solar cells. Journal of Applied Physics, 2014, 116, .	1.1	17
155	Origin of high hole concentrations in Mg-doped GaN films. Physica Status Solidi (B): Basic Research, 2017, 254, 1600668.	0.7	17
156	Crystal structure and composition of BAlN thin films: Effect of boron concentration in the gas flow. Journal of Crystal Growth, 2017, 475, 334-340.	0.7	17
157	Interface properties of n-ZnSe/p-Ge heterojunctions grown by organometallic chemical vapor deposition. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1983, 1, 656.	1.6	16
158	HgTe/CdTe superlattices grown on lattice-mismatched GaAs substrates. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1986, 4, 1306.	1.6	16
159	C ²⁺ Outgrowths in C ⁺ Thin Films of LiNbO ₃ on Al ₂ O ₃ -c. Materials Research Society Symposia Proceedings, 1994, 341, 289.	0.1	16
160	Spatial variation of luminescence in thick GaN films. Applied Physics Letters, 2001, 78, 1222-1224.	1.5	16
161	Spatial variation of luminescence from AlGa _x N grown by facet controlled epitaxial lateral overgrowth. Applied Physics Letters, 2004, 85, 3417-3419.	1.5	16
162	Lateral Current Spreading in III-N Ultraviolet Vertical-Cavity Surface-Emitting Lasers Using Modulation-Doped Short Period Superlattices. IEEE Journal of Quantum Electronics, 2018, 54, 1-7.	1.0	16

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163	Structure of Thermally-Induced Microdefects in Czochralski Silicon. Materials Research Society Symposia Proceedings, 1983, 31, 153.	0.1	15
164	Initial Stages of GaAs Epitaxy on Si. Materials Research Society Symposia Proceedings, 1988, 116, 33.	0.1	15
165	Structure and luminescence of nanocrystalline gallium nitride synthesized by a novel polymer pyrolysis route. Optical Materials, 2006, 29, 19-23.	1.7	15
166	Effect of misfit dislocations on luminescence in m-plane InGaN quantum wells. Applied Physics Letters, 2011, 98, 261914.	1.5	15
167	Improved optical properties of InAs quantum dots for intermediate band solar cells by suppression of misfit strain relaxation. Journal of Applied Physics, 2016, 120, .	1.1	15
168	Current transport mechanisms in GaAs/AlAs tunnel structures grown by metal-organic chemical vapor deposition. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1986, 4, 988.	1.6	14
169	The transition from As-doped GaN, showing blue emission, to GaNAs alloys in films grown by molecular beam epitaxy. Journal of Crystal Growth, 2002, 240, 423-430.	0.7	14
170	The generation of misfit dislocations in facet-controlled growth of AlGaIn-GaN films. Applied Physics Letters, 2004, 85, 4923-4925.	1.5	14
171	Growth of InN on Ge substrate by molecular beam epitaxy. Journal of Crystal Growth, 2005, 279, 311-315.	0.7	14
172	Transmission electron microscopy study of GaInNAs(Sb) thin films grown by atomic hydrogen-assisted molecular beam epitaxy. Applied Physics Letters, 2011, 99, 191907.	1.5	14
173	Strain-related optical properties of ZnO crystals due to nanoindentation on various surface orientations. Journal of Applied Physics, 2013, 113, 183511.	1.1	14
174	Strain management of AlGaIn-based distributed Bragg reflectors with GaN interlayer grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2016, 109, .	1.5	14
175	Electrically conducting n-type AlGaIn/GaN distributed Bragg reflectors grown by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2016, 443, 81-84.	0.7	14
176	Lateral and vertical growth of Mg-doped GaN on trench-patterned GaN films. Applied Physics Letters, 2020, 117, .	1.5	14
177	The impact of interfacial Si contamination on GaN-on-GaN regrowth for high power vertical devices. Applied Physics Letters, 2021, 118, .	1.5	14
178	Polarity determination by atomic location by channeling-enhanced microanalysis. Applied Physics Letters, 2002, 80, 389-391.	1.5	13
179	Thick crack-free AlGaIn films deposited by facet-controlled epitaxial lateral overgrowth. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2136-2140.	0.8	13
180	Raman line shape of the A1 longitudinal optical phonon in GaN. Applied Physics Letters, 2004, 84, 3471-3473.	1.5	13

#	ARTICLE	IF	CITATIONS
181	Basal-plane slip in InGaN-GaN heterostructures in the presence of threading dislocations. Applied Physics Letters, 2007, 90, 171922.	1.5	13
182	Evidence of Two-Dimensional Hole Gas in p-Type AlGaIn/GaN Heterostructures. Applied Physics Express, 2009, 2, 121001.	1.1	13
183	Electrostatic energy profiles at nanometer-scale in group III nitride semiconductors using electron holography. Annalen Der Physik, 2011, 523, 75-86.	0.9	13
184	Optically pumped AlGaIn quantum well lasers at sub-250 nm grown by MOCVD on AlN substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 258-260.	0.8	13
185	Nonpolar vertical GaN-on-GaN pn diodes grown on free-standing (100)-plane GaN substrates. Applied Physics Express, 2018, 11, 111003.	1.1	13
186	Theory and Design of Electron Blocking Layers for III-N-Based Laser Diodes by Numerical Simulation. IEEE Journal of Quantum Electronics, 2018, 54, 1-11.	1.0	13
187	Structural characterization of low-defect-density silicon on sapphire. Journal of Applied Physics, 1983, 54, 4414-4420.	1.1	12
188	Atomic force nanolithography of InP for site control growth of InAs nanostructures. Applied Physics Letters, 2007, 90, 013117.	1.5	12
189	Hydrogen-related, deeply bound excitons in Mg-doped GaN films. Applied Physics Letters, 2013, 103, 082103.	1.5	12
190	Determination of electronic band structure by electron holography of etched-and-regrown interfaces in GaN pn diodes. Applied Physics Letters, 2019, 115, .	1.5	12
191	Thermal Stability of Pt, Pd, and Ni on GaN. Materials Research Society Symposia Proceedings, 1996, 449, 1049.	0.1	11
192	Cathodoluminescence Studies of InGaIn Quantum Wells. Materials Research Society Symposia Proceedings, 1997, 482, 660.	0.1	11
193	Structural and optical properties of coherent GaN islands grown on 6H-SiC(0001)-(111). Applied Physics Letters, 2003, 82, 2889-2891.	1.5	11
194	Influence of stacking faults on the properties of GaN-based UV light-emitting diodes grown on non-polar substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2732-2735.	0.8	11
195	Free carrier accumulation at cubic AlGaIn/GaN heterojunctions. Applied Physics Letters, 2012, 100, 142108.	1.5	11
196	Critical thickness investigation of MBE-grown GaInAs/GaAs and GaAsSb/GaAs heterostructures. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2016, 34, 02L113.	0.6	11
197	Effects of boron concentration upon oxygen precipitation in CZ silicon. Journal of Crystal Growth, 1987, 85, 91-96.	0.7	10
198	Layer disordering of GaAs-AlGaAs superlattices by diffusion of laser-incorporated Si. Journal of Applied Physics, 1988, 64, 3439-3444.	1.1	10

#	ARTICLE	IF	CITATIONS
199	Thin film backside gettering in <i>n</i> -type (100) Czochralski silicon during simulated CMOS process cycles. <i>Journal of Materials Research</i> , 1989, 4, 623-633.	1.2	10
200	Spatial variation of luminescence of InGaN alloys measured by highly-spatially-resolved scanning cathodoluminescence. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2002, 93, 19-23.	1.7	10
201	Carrier dynamics and electrostatic potential variation in InGaN quantum wells grown on {112 $\bar{2}$ } GaN pyramidal planes. <i>Applied Physics Letters</i> , 2006, 89, 231908.	1.5	10
202	Effect of native oxide mechanical deformation on InP nanoindentation. <i>Journal of Applied Physics</i> , 2008, 104, .	1.1	10
203	Temperature Dependence and High-Temperature Stability of the Annealed Ni/Au Ohmic Contact to p-Type GaN in Air. <i>Journal of Electronic Materials</i> , 2016, 45, 2087-2091.	1.0	10
204	Thermal donor formation and annihilation in oxygen-implanted float-zone silicon. <i>Journal of Applied Physics</i> , 1992, 72, 1758-1765.	1.1	9
205	Transmission electron microscopy of the AlN-SiC interface. <i>Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties</i> , 1996, 74, 777-789.	0.7	9
206	Determination of the electronic band structure for a graded modulation-doped AlGa \hat{N} -AlN-GaN superlattice. <i>Applied Physics Letters</i> , 2007, 91, 142121.	1.5	9
207	Synthesis of highly luminescent, undoped, Mg-doped and Si-doped GaN powders. <i>Journal of Crystal Growth</i> , 2007, 304, 225-232.	0.7	9
208	Growth of free-standing highly luminescent undoped and Mg-doped GaN thick films with a columnar structure. <i>Journal of Crystal Growth</i> , 2008, 310, 3131-3134.	0.7	9
209	High quality a-plane GaN films grown on cone-shaped patterned r-plane sapphire substrates. <i>Thin Solid Films</i> , 2011, 519, 2508-2512.	0.8	9
210	Early stages of mechanical deformation in indium phosphide with the zinc blende structure. <i>Journal of Applied Physics</i> , 2012, 112, 063514.	1.1	9
211	Capacitance Voltage Characteristics and Electron Holography on Cubic AlGa \hat{N} /GaN Heterojunctions. <i>Japanese Journal of Applied Physics</i> , 2013, 52, 08JN04.	0.8	9
212	Compositional variations in In _{0.5} Ga _{0.5} N nanorods grown by molecular beam epitaxy. <i>Nanotechnology</i> , 2014, 25, 215705.	1.3	9
213	Inverse-Tapered p-Waveguide for Vertical Hole Transport in High-[Al] AlGa \hat{N} Emitters. <i>IEEE Photonics Technology Letters</i> , 2015, 27, 1768-1771.	1.3	9
214	Development of a high-band gap high temperature III-nitride solar cell for integration with concentrated solar power technology. , 2016, , .		9
215	On the structure of small palladium particles. <i>Scripta Metallurgica</i> , 1989, 23, 1555-1558.	1.2	8
216	Luminescence studies of defects and piezoelectric fields in InGa \hat{N} /GaN single quantum wells. <i>Journal of Crystal Growth</i> , 2001, 230, 481-486.	0.7	8

#	ARTICLE	IF	CITATIONS
217	The nature of arsenic incorporation in GaN. Applied Physics Letters, 2001, 79, 3239-3241.	1.5	8
218	Nanoscale dislocation patterning by scratching in an atomic force microscope. Journal of Applied Physics, 2009, 106, 076106.	1.1	8
219	Performance characteristics of InAlGaN laser diodes depending on electron blocking layer and waveguiding layer design grown by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2011, 315, 272-277.	0.7	8
220	A new exposure model to evaluate smoked illicit drugs in rodents: A study of crack cocaine. Journal of Pharmacological and Toxicological Methods, 2016, 77, 17-23.	0.3	8
221	Lateral mode stabilization of diode lasers by means of apertured facet reflectors. IEEE Journal of Quantum Electronics, 1979, 15, 1205-1207.	1.0	7
222	Reactive interface formation of Pt/SiO ₂ /111: Nucleation and morphology. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1987, 5, 1039.	1.6	7
223	Lattice Mismatch Effects in GaAs Epitaxy on Si and GaP. Materials Research Society Symposia Proceedings, 1988, 122, 21.	0.1	7
224	Heteroepitaxial Metal Oxides on Silicon by Laser Ablation. Materials Research Society Symposia Proceedings, 1990, 191, 187.	0.1	7
225	Anisotropic diffusion and drift of photogenerated carriers near coreless dislocations in InGaN quantum well. Applied Physics Letters, 2001, 79, 75-77.	1.5	7
226	Growth of InAs nanostructures on InP using atomic-force nanolithography. Applied Physics A: Materials Science and Processing, 2007, 89, 945-949.	1.1	7
227	Photoluminescence of near-lattice-matched GaN/AlInN quantum wells grown on free-standing GaN and on sapphire substrates. Applied Physics Letters, 2008, 92, .	1.5	7
228	Stimulated emission at 257 nm from optically-pumped AlGaN/AlN heterostructure on AlN substrate. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 1768-1770.	0.8	7
229	Demonstration of GaN-based metal-insulator-semiconductor junction by hydrogen plasma treatment. Applied Physics Letters, 2020, 117, .	1.5	7
230	Surface morphology control of green LEDs with p-InGaN layers grown by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2008, 310, 5166-5169.	0.7	6
231	Polarization effects in 2-DEG and 2-DHG AlGaIn/AlN/GaN multi-heterostructures measured by electron holography. Physica Status Solidi (B): Basic Research, 2010, 247, 1722-1724.	0.7	6
232	Misfit strain relaxation in m-plane epitaxy of InGaN on ZnO. Applied Physics Letters, 2010, 96, .	1.5	6
233	Correlated Structural, Electronic, and Optical Properties of AlN/GaN Multiple Quantum Disks in GaN Nanowires. Applied Physics Express, 2012, 5, 025001.	1.1	6
234	Early nucleation stages of low density InAs quantum dots nucleation on GaAs by MOVPE. Journal of Crystal Growth, 2016, 434, 47-54.	0.7	6

#	ARTICLE	IF	CITATIONS
235	High Reflectivity Hybrid AlGaIn/Silver Distributed Bragg Reflectors for Use in the UV-Visible Spectrum. IEEE Journal of Quantum Electronics, 2017, 53, 1-8.	1.0	6
236	Identification of point defects using high-resolution electron energy loss spectroscopy. Physical Review B, 2019, 99, .	1.1	6
237	Temperature dependence of thin-film ferromagnetic resonance linewidths. Solid State Communications, 1976, 18, 521-522.	0.9	5
238	Transmission Electron Microscopy of Excimer Laser Crystallized Amorphous Si Thin Films. Materials Research Society Symposia Proceedings, 1990, 192, 669.	0.1	5
239	Strain and defect generation during interdiffusion of GaAs into Al _{0.5} In _{0.5} P. Applied Physics Letters, 1993, 62, 2060-2062.	1.5	5
240	Low energy electron-excited nano-luminescence spectroscopy of GaN surfaces and interfaces. Applied Surface Science, 2001, 175-176, 442-449.	3.1	5
241	Al _x Ga _{1-x} N (0 ≤ x ≤ 1) nanocrystalline powder by pyrolysis route. Journal of Crystal Growth, 2007, 308, 198-203.	0.7	5
242	SEM characterization of silicon nanostructures: can we meet the challenge?. Scanning, 2008, 30, 310-316.	0.7	5
243	Measurement of the solubility of ammonia and nitrogen in gallium at atmospheric pressure. Journal of Alloys and Compounds, 2009, 467, 611-613.	2.8	5
244	Preface: Phys. Status Solidi C 7/1. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 7-8.	0.8	5
245	Effect of Growth Temperature on the Electron-Blocking Performance of InAlN Layers in Green Emitting Diodes. Applied Physics Express, 2010, 3, 031003.	1.1	5
246	Growth of linearly ordered arrays of InAs nanocrystals on scratched InP. Journal of Applied Physics, 2010, 107, 054313.	1.1	5
247	Plastic hardening in cubic semiconductors by nanoscratching. Journal of Applied Physics, 2011, 109, 013502.	1.1	5
248	The effect of nanoscratching direction on the plastic deformation and surface morphology of InP crystals. Journal of Applied Physics, 2013, 114, .	1.1	5
249	Effect of Group-III precursors on unintentional gallium incorporation during epitaxial growth of InAlN layers by metalorganic chemical vapor deposition. Journal of Applied Physics, 2015, 118, .	1.1	5
250	Correlation between size distribution and luminescence properties of spool-shaped InAs quantum dots. Semiconductor Science and Technology, 2017, 32, 055013.	1.0	5
251	Realizing crack-free high-aluminum-mole-fraction AlGaIn on patterned GaN beyond the critical layer thickness. Journal of Applied Physics, 2022, 131, .	1.1	5
252	Reduction of GaAs diode laser spontaneous emission. Applied Physics Letters, 1980, 37, 10-12.	1.5	4

#	ARTICLE	IF	CITATIONS
253	Integrated output power detection for AlGaAs laser array. IEEE Journal of Quantum Electronics, 1980, 16, 502-504.	1.0	4
254	Effectiveness of CVD thin Film Backside Gettering and Its Interaction with Intrinsic Gettering. Materials Research Society Symposia Proceedings, 1986, 71, 33.	0.1	4
255	Structure of the (100) GaAs on GaP interface. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1988, 6, 1310.	1.6	4
256	The Influence of Substrate Surface Chemistry on GaAs - on - Si Growth. Materials Research Society Symposia Proceedings, 1988, 116, 51.	0.1	4
257	Epitaxial Growth of Ferroelectric Thin Films on GaAs with MgO Buffer Layers by Pulsed Laser Deposition. Materials Research Society Symposia Proceedings, 1991, 243, 495.	0.1	4
258	Structural characterization of GaAs/GaP superlattices. Journal Physics D: Applied Physics, 1993, 26, A167-A172.	1.3	4
259	Defect generation and suppression during the impurity-induced layer disordering of quantum-sized GaAs/GaN layers. Applied Physics Letters, 1994, 65, 2696-2698.	1.5	4
260	Low-energy electron-excited nanoluminescence studies of GaN and related materials. Applied Surface Science, 2002, 190, 498-507.	3.1	4
261	Nitrogen surfactant effects in GaInP. Journal of Applied Physics, 2004, 96, 7229-7234.	1.1	4
262	Optical Properties of GaN Nanowhiskers Produced by Photoelectrochemical Etching. ECS Transactions, 2006, 3, 415-419.	0.3	4
263	Very Thin 2D GaAs Films on Si During the Early Stages of Growth by MBE. Materials Research Society Symposia Proceedings, 1989, 159, 15.	0.1	3
264	Xps Analysis of Y-Ba-Cu-O and Zr-O Thin Films and Interfaces with Silicon Substrates. Materials Research Society Symposia Proceedings, 1989, 169, 1005.	0.1	3
265	Interface Formation and the Heteroepitaxy of ZnSe on Si.. Materials Research Society Symposia Proceedings, 1990, 198, 195.	0.1	3
266	In-Situ Growth Of Superconducting YBa ₂ Cu ₃ O _y Films By Pulsed Laser Deposition. Proceedings of SPIE, 1990, 1187, 136.	0.8	3
267	Glide along non-basal slip planes in InGaN epilayers. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2440-2443.	0.8	3
268	Performance improvement of InGaN-based laser diodes by epitaxial layer structure design. Proceedings of SPIE, 2010, , .	0.8	3
269	Optically pumped deep-ultraviolet AlGaIn multi-quantum-well lasers grown by metalorganic chemical vapor deposition. , 2014, , .		3
270	Development for ultraviolet vertical cavity surface emitting lasers. Proceedings of SPIE, 2016, , .	0.8	3

#	ARTICLE	IF	CITATIONS
271	Dislocation baskets in thick In _x Ga _{1-x} N epilayers. Journal of Applied Physics, 2018, 124, .	1.1	3
272	Influence of substrate misorientation on the optical properties of Mg-doped GaN. Journal of Applied Physics, 2020, 127, .	1.1	3
273	Investigation of polycrystalline GaIn _{1-x} P for potential use as a solar cell absorber with tunable bandgap. Journal of Applied Physics, 2020, 127, 073102.	1.1	3
274	Characterization of MOCVD regrown p-GaN and the interface properties for vertical GaN power devices. Semiconductor Science and Technology, 2021, 36, 014005.	1.0	3
275	Imaging of interfaces in semiconductor materials using high resolution transmission electron microscopy. Ultramicroscopy, 1982, 9, 215-219.	0.8	2
276	Interaction Between Deposited Film Extrinsic Gettering and Intrinsic Gettering in CZ Silicon During Simulated CMOS Process Cycles. Materials Research Society Symposia Proceedings, 1985, 59, 353.	0.1	2
277	Silicon Quantum Wires Oxidation and Transport Studies. Materials Research Society Symposia Proceedings, 1992, 283, 57.	0.1	2
278	Luminescence Properties of Charged Dislocations in Semi-Insulating GaN : Zn. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 508-511.	0.8	2
279	Deep green emission at 570nm from InGaN/GaN MQW active region grown on bulk AlN substrate. , 2005, 5941, 37.		2
280	A Novel Method to Synthesize Blue-Luminescent Doped GaN Powders. Materials Research Society Symposia Proceedings, 2005, 864, 6101.	0.1	2
281	Reduction of structural defects in a-plane GaN epitaxy by use of periodic hemispherical patterns in r-plane sapphire substrates. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2011, 29, 021005.	0.6	2
282	Improved Hole Transport by $\{m p\} \{m In\}_x \{m Ga\}_{1-x} \{m N\}$ Layer in Multiple Quantum Wells of Visible LEDs. IEEE Photonics Technology Letters, 2013, 25, 1789-1792.	1.3	2
283	The growth of In _{0.5} Ga _{0.5} N and InN layers on (111)Si using nanorod intermediate arrays. Journal of Crystal Growth, 2013, 384, 55-60.	0.7	2
284	High Energy and Spatial Resolution EELS Band Gap Measurements Using a Nion Monochromated Cold Field Emission HERMES Dedicated STEM. Microscopy and Microanalysis, 2014, 20, 70-71.	0.2	2
285	Evaluating the performance of InGaN/GaN multi-quantum-well solar cells operated at elevated temperatures via DC and small-signal AC analysis. Japanese Journal of Applied Physics, 2019, 58, 101003.	0.8	2
286	Novel semiconductors for sustainable solar energy technologies. Journal of Physics: Conference Series, 2019, 1173, 012001.	0.3	2
287	Effect of InAs quantum dots capped with GaAs on atomic-scale ordering in Ga _{0.5} In _{0.5} P. Journal of Applied Physics, 2019, 125, 053104.	1.1	2
288	Silicon-Sapphire Interface: A High Resolution Electron Microscopy Study. Materials Research Society Symposia Proceedings, 1980, 2, 285.	0.1	1

#	ARTICLE	IF	CITATIONS
289	Imaging of Defects in Cadmium Telluride using High Resolution Transmission Electron Microscopy. Materials Research Society Symposia Proceedings, 1980, 2, 503.	0.1	1
290	Laser patterned desorption within an upflow metalorganic chemical vapor deposition reactor. Applied Surface Science, 1989, 43, 432-438.	3.1	1
291	Applications of In-Situ UHV and High Resolution Tem to the Study of Small Particles. Materials Research Society Symposia Proceedings, 1989, 139, 81.	0.1	1
292	Properties of Interfaces between Superlattice Heterostructures and Uniform Alloy Materials as Realized by Impurity Induced Disorder. Materials Research Society Symposia Proceedings, 1990, 198, 85.	0.1	1
293	Microstructure of Impurity Induced Disorder at The GaAs/InGaAlP Interface. Materials Research Society Symposia Proceedings, 1991, 221, 349.	0.1	1
294	Initial Stages of Growth of ZnSe on Si. Materials Research Society Symposia Proceedings, 1992, 242, 191.	0.1	1
295	Mapping of Donor Impurities in GaN By Raman Imaging. Materials Research Society Symposia Proceedings, 1996, 449, 731.	0.1	1
296	Response to "Comment on "Low Stokes shift in thick and homogeneous InGaN epilayers" [Appl. Phys. Lett 81, 1353 (2002)]. Applied Physics Letters, 2002, 81, 1355-1356.	1.5	1
297	Distinct Magnesium Incorporation Behavior in Laterally Grown AlGaN. Materials Research Society Symposia Proceedings, 2002, 743, L1.11.1.	0.1	1
298	Optical and Microstructural Properties of N- and Ga-Polarity GaN. Materials Research Society Symposia Proceedings, 2003, 798, 580.	0.1	1
299	Synthesis, Structure and Luminescence of High Brightness Gallium Nitride Powder. Materials Research Society Symposia Proceedings, 2003, 798, 243.	0.1	1
300	Electrostatic Fields and Compositional Fluctuations in InGaN Quantum Wells. AIP Conference Proceedings, 2005, , .	0.3	1
301	Localization versus carrier-screening effects in InGaN quantum wells " A time-resolved cathodoluminescence study. AIP Conference Proceedings, 2005, , .	0.3	1
302	Crystal Structure of Low-Resistance Au-Ni/p-GaN Contacts. AIP Conference Proceedings, 2005, , .	0.3	1
303	Donor-related cathodoluminescence of p-AlGaN electron blocking layer embedded in ultraviolet laser diode structure. Applied Physics Letters, 2009, 94, 211103.	1.5	1
304	Microstructure and polarization fields in nitride semiconductors. Journal of Physics: Conference Series, 2011, 326, 012001.	0.3	1
305	Room-temperature optically pumped AlGaN-AlN multiple-quantum-well lasers operating at <260nm grown by metalorganic chemical vapor deposition. Proceedings of SPIE, 2013, , .	0.8	1
306	Indium Nitride and Indium Gallium Nitride layers grown on nanorods. Journal of Physics: Conference Series, 2013, 471, 012025.	0.3	1

#	ARTICLE	IF	CITATIONS
307	High Spatial/Energy Resolution Band Gap Measurements: Delocalization and Other Effects in a Monochromated Cold FEG Nion Dedicated STEM. Microscopy and Microanalysis, 2015, 21, 657-658.	0.2	1
308	Stability of alloyed and nonalloyed ohmic contacts to n-type GaN at high temperature in air. Japanese Journal of Applied Physics, 2017, 56, 126502.	0.8	1
309	Corrections to "Lateral Current Spreading in III-N Ultraviolet Vertical-Cavity Surface-Emitting Lasers Using Modulation-Doped Short Period Superlattices" [Aug 18 Art. no. 2400507]. IEEE Journal of Quantum Electronics, 2019, 55, 1-1.	1.0	1
310	The effect of low-angle off-axis GaN substrate orientation on the surface morphology of Mg-doped GaN epilayers. Journal of Applied Physics, 2020, 128, 055301.	1.1	1
311	Nanostructured materials for high efficiency solar cells. , 2021, , 201-227.		1
312	Precipitation of hydrogen in crystalline silicon. Proceedings Annual Meeting Electron Microscopy Society of America, 1988, 46, 476-477.	0.0	1
313	High Resolution Imaging of Semiconductor Interfaces. Proceedings Annual Meeting Electron Microscopy Society of America, 1981, 39, 124-127.	0.0	1
314	Crystalline Particles in Thermally Grown Silicon Dioxide. Materials Research Society Symposia Proceedings, 1982, 14, 201.	0.1	0
315	Lattice Structure at ZnSe-GaAs Heterojunction Interfaces Prepared by Organometallic Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 1982, 18, 133.	0.1	0
316	Study of Initial Stages of Heteroepitaxy Using Graded Thickness Samples. Materials Research Society Symposia Proceedings, 1987, 102, 437.	0.1	0
317	Temperature Dependent C-V Characteristics of YBCO/YSZ/Si MIS Capacitors. Materials Research Society Symposia Proceedings, 1992, 275, 583.	0.1	0
318	Experimental evidence of the structure of annihilation of antiphase boundaries in GaAs on Si. Materials Letters, 1993, 15, 353-355.	1.3	0
319	Amorphous Domains in GaN Layers Grown on 6H-SiC by MBE. Materials Research Society Symposia Proceedings, 1997, 482, 487.	0.1	0
320	Environment About Indium in $Ga_{1-x}In_xN$ from In and Ga K-Edge XAFS. European Physical Journal Special Topics, 1997, 7, C2-1253-C2-1254.	0.2	0
321	Profiling electric fields in GaN/InGaN/GaN single quantum wells by electron holography. Materials Research Society Symposia Proceedings, 2000, 639, 11201.	0.1	0
322	Hollow core dislocations in Mg-doped AlGaIn. Materials Research Society Symposia Proceedings, 2002, 743, L10.9.1.	0.1	0
323	Preface: phys. stat. sol. (b) 230/2/2002. Physica Status Solidi (B): Basic Research, 2002, 230, 307-308.	0.7	0
324	Field effect and localization in InGaIn/GaN quantum wells. , 0, , .		0

#	ARTICLE	IF	CITATIONS
325	Effects of Si-doping on the Microstructure of AlGaIn/GaN Multiple-quantum-well. Materials Research Society Symposia Proceedings, 2003, 798, 512.	0.1	0
326	Platelet Inversion Domains Induced by Mg-doping in ELOG AlGaIn Films. Materials Research Society Symposia Proceedings, 2003, 798, 478.	0.1	0
327	Microstructure of In/sub x/Ga/sub 1-x/N thick epitaxial layers. , 0, , .		0
328	Interface atomic arrangement between the nitride semiconductor and silicon. , 0, , .		0
329	Growth-direction dependence of optical properties in epitaxially laterally overgrown GaN. , 0, , .		0
330	CBED study of grain misorientations in AlGaIn epilayers. Ultramicroscopy, 2005, 103, 23-32.	0.8	0
331	The Electronic Nature of metal/p-GaN Junctions. AIP Conference Proceedings, 2005, , .	0.3	0
332	The Nature of Crystalline Defects in a-plane GaN Films. AIP Conference Proceedings, 2005, , .	0.3	0
333	Light Emission from GaN Microcrystals. AIP Conference Proceedings, 2005, , .	0.3	0
334	Strain Relaxation Mechanisms in InGaIn Epilayers. AIP Conference Proceedings, 2005, , .	0.3	0
335	TEM Characterization of ZnO Crystals Synthesize with Controlled Size and Morphology. Microscopy and Microanalysis, 2007, 13, .	0.2	0
336	Preface: Phys. Status Solidi A 206/2. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 193-194.	0.8	0
337	Microstructure of nanoscratched semiconductors. Journal of Physics: Conference Series, 2011, 326, 012061.	0.3	0
338	(Invited) Carrier Dynamics and Photon Management for Improvement in Quantum Efficiencies of GaN-Based Visible Light-Emitting Diodes. ECS Transactions, 2014, 61, 109-116.	0.3	0
339	Growth of III-Nitrides. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 331-333.	0.8	0
340	Strain Relaxation in InAs Quantum Dots and its Suppression by Indium Flushing. Microscopy and Microanalysis, 2015, 21, 983-984.	0.2	0
341	Structural and Optical Properties of AlGaIn MQWs Grown by MOCVD Using One and Two TMG Sources. Microscopy and Microanalysis, 2015, 21, 1681-1682.	0.2	0
342	Optically pumped low-threshold UV lasers. , 2015, , .		0

#	ARTICLE	IF	CITATIONS
343	From InAs extended monolayer flat 2D terraces to 3D islands grown on GaAs substrates. , 2015, , .		0
344	III-nitride deep UV laser on sapphire substrate. , 2015, , .		0
345	Local Strain Relaxation by A-type Dislocation Clusters in In _x Ga _{1-x} N/GaN Film with Indium Compositions of x = 0.07 and 0.12. Microscopy and Microanalysis, 2016, 22, 1572-1573.	0.2	0
346	AlGaSb based solar cells grown on GaAs by Molecular Beam Epitaxy. , 2016, , .		0
347	Growth and Characterization of III-N Ultraviolet Lasers and Avalanche Photodiodes by MOCVD. , 2017, , .		0
348	High Resolution EELS of Point Defects in a Nitride Semiconductor Material. Microscopy and Microanalysis, 2018, 24, 430-431.	0.2	0
349	A Hybrid Concentrating Solar Thermal/ Photovoltaic System Using a High Temperature III-nitride Photovoltaic Device. , 2014, , .		0
350	Structural aspects of silicon diffusion in quaternary III-V thin-film semiconductors. Proceedings Annual Meeting Electron Microscopy Society of America, 1991, 49, 850-851.	0.0	0
351	Onset of deep UV surface stimulated emission from AlGaIn multiple quantum wells. , 2016, , .		0
352	Growth of single-phase wurtzite BAlN with 7.2%-B contents. , 2016, , .		0
353	Lattice Imaging of Heteroepitaxial Silicon on Sapphire. Proceedings Annual Meeting Electron Microscopy Society of America, 1981, 39, 128-129.	0.0	0
354	HREM at orthogonal projections of GaAs islands on silicon. Proceedings Annual Meeting Electron Microscopy Society of America, 1989, 47, 586-587.	0.0	0